

32H8205-VB Datasheet

Dual N-Channel MOSFET

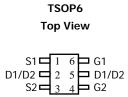
PRODUCT SUMMARY				
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A)		
20	0.024 at V _{GS} = 4.5 V	6.0		
	0.028 at V _{GS} = 2.5 V	5.0		

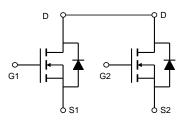
FEATURES

- Halogen-free Option Available
- Trench Power MOSFETs 100 $\%~{\rm R_g}$ Tested
- .
- Compliant to RoHS Directive 2002/95/EC



COMPLIANT





ABSOLUTE MAXIMUM RATINGS T	A = 25 °C, unles	s otherwise n	oted			
Parameter		Symbol	10 s	Steady State	Unit	
Drain-Source Voltage		V _{DS}	20		V	
Gate-Source Voltage		V _{GS}	± 12			
Continuous Droin Current /T 150 °C)a	T _A = 25 °C	- I _D	6.0	5.2	٨	
Continuous Drain Current $(T_J = 150 \text{ °C})^a$	T _A = 70 °C		4.8	4.2		
Pulsed Drain Current		I _{DM}	30		A	
Continuous Source Current (Diode Conduction) ^a		۱ _S	1.5	1.0		
Maria Diaria di ad	T _A = 25 °C	P _D	1.5	1.0	W	
Maximum Power Dissipation ^a	T _A = 70 °C	гD	0.96	0.64	vv	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Тур.	Max.	Unit
Maximum has the te Aashingta	t ≤ 10 s	R _{thJA}	72	83	
Maximum Junction-to-Ambient ^a	Steady State	' thJA	100	120	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	55	70	

Notes:

a. Surface Mounted on FR4 board, t \leq 10 s.

* Pb containing terminations are not RoHS compliant, exemptions may apply.



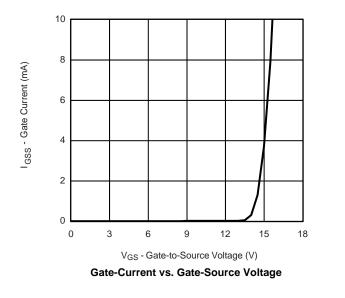
Parameter	Symbol	Test Conditions		Typ. ^a	Max.	Unit	
Static			•	•			
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \ \mu A$	0.5		1.5	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 4.5 \text{ V}$			± 200	nA	
Zero Gate Voltage Drain Current		$V_{DS} = 20 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$			1	μA	
	IDSS	$V_{DS} = 20 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 70 \text{ °C}$			25		
On-State Drain Current ^b	I _{D(on)}	$V_{DS}{\leq}5$ V, $V_{GS}{=}4.5$ V	30			А	
Drain-Source On-State Resistance ^b	Б	$V_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 5.5 \text{ A}$	A			-	
	R _{DS(on)}	V _{GS} = 2.5 V, I _D = 3.5 A 0.028				Ω	
Forward Transconductance ^b	g _{fs}	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 5.5 \text{ A}$		30		S	
Diode Forward Voltage ^b	V _{SD}	I _S = 1.5 A, V _{GS} = 0 V		0.71	1.2	V	
Dynamic ^a							
Total Gate Charge	Qg			12	18		
Gate-Source Charge	Q _{gs}	$V_{DS} = 10 \text{ V}, \text{ V}_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 5.5 \text{ A}$		2.2		nC	
Gate-Drain Charge	Q _{gd}			3.6			
Turn-On Delay Time	t _{d(on)}			245	365		
Rise Time	t _r	V_{DD} = 10 V, R_L = 10 Ω		330	495		
Turn-Off Delay Time	t _{d(off)}	$I_D \cong$ 1 A, V_{GEN} = 4.5 V, R_G = 6 Ω		860	1300	ns	
Fall Time	t _f			510	765		

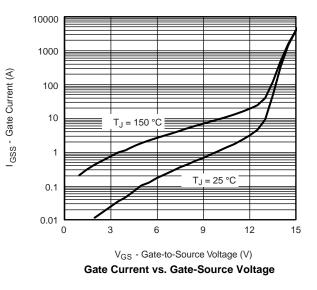
Notes:

a. For design aid only; not subject to production testing.

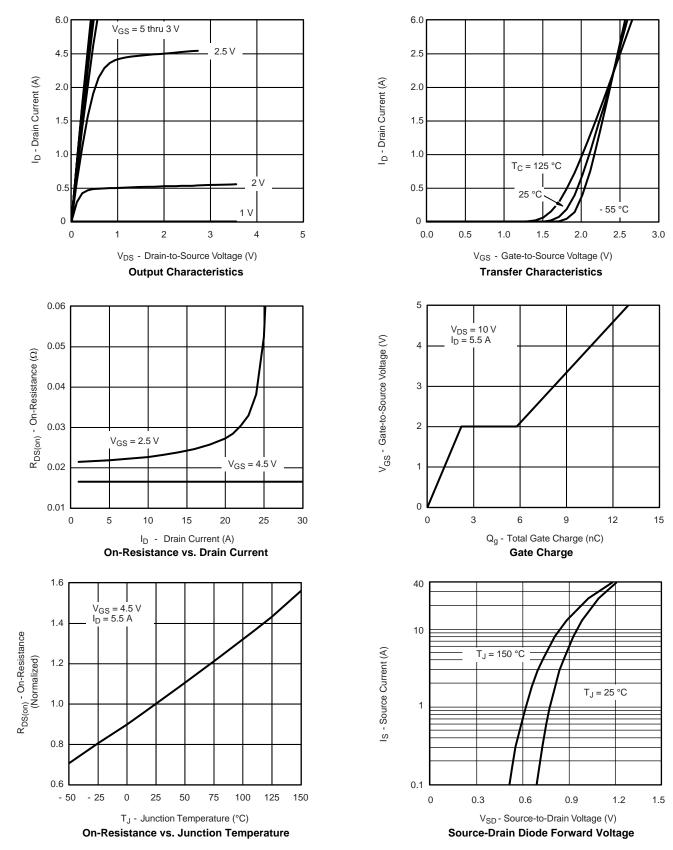
b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

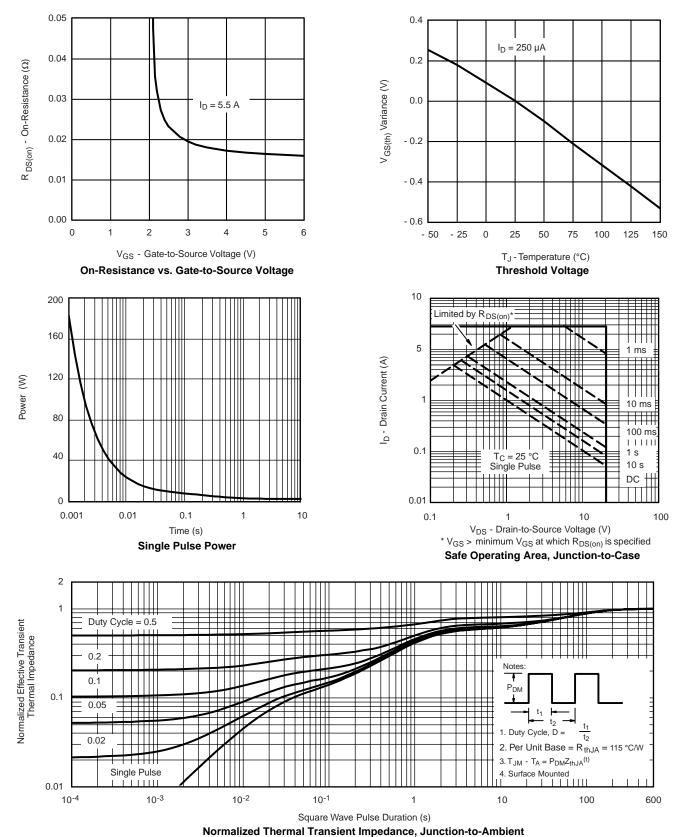




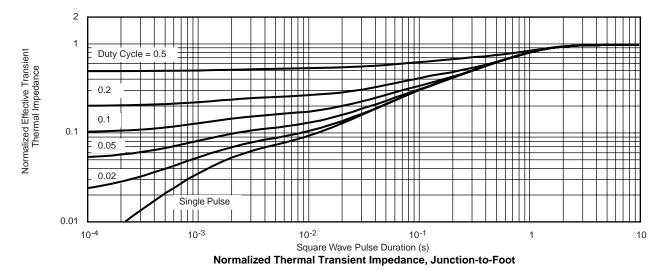






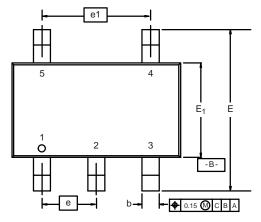




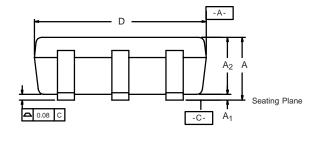


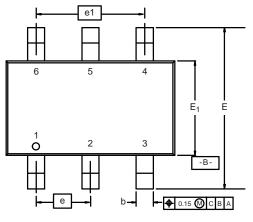


TSOP: 5/6-LEAD JEDEC Part Number: MO-193C

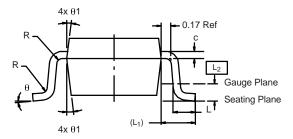








6-LEAD TSOP



	MILLIMETERS			INCHES			
Dim	Min	Nom	Max	Min	Nom	Max	
Α	0.91	-	1.10	0.036	-	0.043	
A ₁	0.01	-	0.10	0.0004	-	0.004	
A ₂	0.90	-	1.00	0.035	0.038	0.039	
b	0.30	0.32	0.45	0.012	0.013	0.018	
С	0.10	0.15	0.20	0.004	0.006	0.008	
D	2.95	3.05	3.10	0.116	0.120	0.122	
Е	2.70	2.85	2.98	0.106	0.112	0.117	
E ₁	1.55	1.65	1.70	0.061	0.065	0.067	
е	0.95 BSC			0.0374 BSC			
e ₁	1.80	1.90	2.00	0.071	0.075	0.079	
L	0.32	-	0.50	0.012	-	0.020	
L ₁		0.60 Ref		0.024 Ref			
L ₂	0.25 BSC			0.010 BSC			
R	0.10	-	-	0.004	-	-	
θ	0°	4°	8°	0°	4°	8°	
θ_1	7° Nom			7° Nom			
ECN: C-06593-Rev. I, 18-Dec-06 DWG: 5540							



RECOMMENDED MINIMUM PADS FOR TSOP-6



Recommended Minimum Pads Dimensions in Inches/(mm)



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